

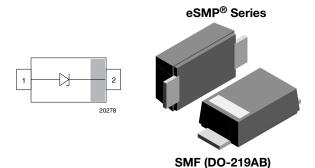
www.vishay.com

Vishay Semiconductors

AUTOMOTIVE

HALOGEN FREE

# 400 W TransZorb® Transient Voltage Suppressor (TVS) **Diode in SMF-Package**



#### **MARKING** (example only)



Bar = cathode marking YYY = type code (see table below) XX = date code

### **LINKS TO ADDITIONAL RESOURCES**



VTVS5V0GSMF-

±2%

Н





PRIMARY CHARACTERISTICS							
$V_{BR}$	6.4 V to 78.2 V						
$V_{WM}$	3.3 V to 63 V						
P <sub>PPM</sub>	400 W						
T <sub>J</sub> max.	175 °C						
Polarity	Unidirectional						
Package	SMF (DO-219AB)						

#### **FEATURES**

- 400 W peak pulse power capability with a 10/1000 µs waveform
- Tolerance of the avalanche breakdown voltage ± 5 % VTVSxxxA...
  - ± 2 % VTVSxxxG...
- Low-profile package
- Wave and reflow solderable
- ESD-protection acc. IEC 61000-4-2 ± 30 kV contact discharge
  - ± 30 kV air discharge
- Excellent clamping capability
- "Low-Noise" technology very fast response time
- AEC-Q101 qualified available
- Compatible to SOD-123W package case outline or SOD-123F and SOD-123FL
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

-18

VTVS5V0GSMF-HM3-18

ORDERING INFORMATION											
		ENVIRON	MENTAL AND QUALITY	CODE	PACKAGI	NG CODE					
PART NUMBER (EXAMPLE)	TOLERANC E V <sub>BR</sub>	AEC-Q101 QUALIFIED	RoHS-COMPLIANT + LEAD (Pb)-FREE TERMINATIONS	TIN PLATED	3K PER 7" REEL (8 mm TAPE), MOQ	10K PER 13" REEL (8 mm TAPE), MOQ	ORDERING CODE (EXAMPLE)				
			HALOGEN-FREE		= 30K	= 50K					
VTVS5V0ASMF-	± 5 %		М	3	-08		VTVS5V0ASMF-M3-08				
VTVS5V0ASMF-	± 5 %	Н	М	3	-08		VTVS5V0ASMF-HM3-08				
VTVS5V0ASMF-	± 5 %		М	3		-18	VTVS5V0ASMF-M3-18				
VTVS5V0ASMF-	± 5 %	Н	М	3		-18	VTVS5V0ASMF-HM3-18				
VTVS5V0GSMF-	± 2 %		М	3	-08		VTVS5V0GSMF-M3-08				
VTVS5V0GSMF-	± 2 %	Н	М	3	-08		VTVS5V0GSMF-HM3-08				
VTVS5V0GSMF-	± 2 %		M	3		-18	VTVS5V0GSMF-M3-18				

Μ





## Vishay Semiconductors

PACKAGE DATA												
PACKAGE NAME	MOLDING COMPOUND	WEIGH T (mg)	HEIGH T MAX. (mm)	LENGT H MAX. (mm)	WIDT H MAX. (mm)	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	WHISKER TEST ACC. JESD 201	SOLDERING CONDITIONS			
SMF (DO-219AB)	Halogen-free	15	1.08	3.9	1.9	UL 94 V-0	MSL level 1 (acc. J-STD-020)	class 2	Peak temperature max. 260 °C			

ABSOLUTE MAXIMUM RATINGS (T <sub>amb</sub> = 25 °C, unless otherwise specified)									
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT					
Peak pulse current	t <sub>p</sub> = 10/1000 μs waveform	I <sub>PPM</sub>	see "Electrical Characteristics"	А					
Peak pulse power	t <sub>p</sub> = 10/1000 μs waveform	P <sub>PP</sub>	400	W					
FOD :	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV					
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V <sub>ESD</sub>	± 30	kV					
Thermal resistance	Mounted on infinite heat sink	$R_{thJL}$	20	K/W					
Forward clamping voltage	$I_F = 50 \text{ A}, t_p = 1 \text{ ms}$	V <sub>F</sub>	1.8	V					
Operating temperature	Junction temperature	TJ	-55 to +175	°C					
Storage temperature		T <sub>STG</sub>	-55 to +175	°C					

ELECTRICA	<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)											
PART NUMBER	TYPE CODE	REVERSE BREAKDOWN VOLTAGE at T <sub>J</sub> = 25 °C, I <sub>T</sub> = 1 mA		STAND-OFF VOLTAGE	MAXIMUM REVERSE CURRENT at V <sub>RWM</sub>	MAXIMUM PEAK PULSE CURRENT $t_p = 10/1000 \mu s$	MAXIMUM REVERSE CLAMPING VOLTAGE at I <sub>PPM</sub>	TYPICAL CAP. at V <sub>R</sub> = 0 V, f = 1 MHz	PROTECTION PATHS			
	HALOGEN- FREE	V <sub>BR</sub> (V) MIN.	V <sub>BR</sub> (V) MAX.	V <sub>RWM</sub> (V)	I <sub>R</sub> (μΑ)	I <sub>PPM</sub> (A)	۷ <sub>0</sub>	C <sub>D</sub> (pF)	N <sub>channel</sub>			
VTVS3V3ASMF	9Z5	6.4	7.0	3.3	0.05	42.95	8.9	2095	1			
VTVS5V0ASMF	905	6.4	7.0	5.00	5	42.95	8.9	2095	1			
VTVS8V5ASMF	915	9.5	10.5	8.50	0.1	28.24	13.5	1270	1			
VTVS9V4ASMF	925	10.5	11.6	9.40	0.1	25.48	14.9	1130	1			
VTVS10ASMF	935	11.4	12.7	10.30	0.05	23.20	16.3	988	1			
VTVS11ASMF	945	12.6	13.9	11.20	0.05	21.13	18.0	910	1			
VTVS12ASMF	955	14.0	15.4	12.40	0.05	19.01	20.1	807	1			
VTVS14ASMF	965	15.4	17.0	13.80	0.05	17.16	22.2	752	1			
VTVS15ASMF	975	17.1	18.8	15.10	0.05	15.47	25	684	1			
VTVS17ASMF	985	19.0	21.0	16.90	0.05	13.79	28	606	1			
VTVS19ASMF	995	20.9	23.2	18.70	0.05	12.44	31	558	1			
VTVS21ASMF	9A5	23.0	25.4	20.50	0.05	11.33	34	513	1			
VTVS23ASMF	9B5	25.7	28.4	22.60	0.05	10.09	38	480	1			
VTVS25ASMF	9C5	28.5	31.5	25.20	0.05	9.07	42	433	1			
VTVS28ASMF	9D5	31.4	34.7	27.90	0.05	8.21	47	412	1			
VTVS31ASMF	9E5	34.2	37.8	30.60	0.05	7.51	51	380	1			
VTVS33ASMF	9F5	37.1	41.0	33.30	0.05	6.91	55	379	1			
VTVS36ASMF	9G5	40.9	45.2	36.00	0.05	6.24	61	342	1			
VTVS40ASMF	9H5	44.7	49.4	39.60	0.05	5.70	67	309	1			
VTVS43ASMF	9J5	48.5	53.6	43.20	0.05	5.23	73	292	1			
VTVS47ASMF	9K5	53.2	58.8	46.80	0.05	4.76	80	293	1			
VTVS52ASMF	9L5	58.9	65.1	52.20	0.05	4.28	89	242	1			
VTVS58ASMF	9M5	64.6	71.4	57.60	0.05	3.89	98	245	1			
VTVS63ASMF	9N5	70.8	78.2	63.00	0.05	3.54	108	227	1			



## VTVS3V3ASMF to VTVS63GSMF

## Vishay Semiconductors

		REVERSE (Ta				MAXIMUM	MAXIMUM		
PART NUMBER	TYPE CODE	BREAKDOWN VOLTAGE at T <sub>J</sub> = 25 °C, I <sub>T</sub> = 1 mA		STAND-OFF VOLTAGE	MAXIMUM REVERSE CURRENT at V <sub>RWM</sub>	PEAK PULSE CURRENT t <sub>p</sub> = 10/1000 µs	REVERSE CLAMPING VOLTAGE at IPPM	TYPICAL CAP. at V <sub>R</sub> = 0 V, f = 1 MHz	PROTECTION PATHS
	HALOGEN- FREE	V <sub>BR</sub> (V) MIN.	V <sub>BR</sub> (V) MAX.	V <sub>RWM</sub> (V)	I <sub>R</sub> (μ <b>A</b> )	I <sub>PPM</sub> (A)	۷ <sub>0</sub>	C <sub>D</sub> (pF)	N <sub>channel</sub>
VTVS3V3GSMF	9Z2	6.57	6.84	3.3	0.05	43.99	8.9	2095	1
VTVS5V0GSMF	902	6.57	6.84	5.00	5	43.99	8.9	2095	1
VTVS8V5GSMF	912	9.80	10.20	8.50	0.1	29.10	13.5	1270	1
VTVS9V4GSMF	922	10.83	11.28	9.40	0.1	26.23	14.9	1130	1
VTVS10GSMF	932	11.81	12.30	10.30	0.05	23.98	16.3	988	1
VTVS11GSMF	942	12.99	13.52	11.20	0.05	21.75	18.0	910	1
VTVS12GSMF	952	14.41	15.00	12.40	0.05	19.53	20.1	807	1
VTVS14GSMF	962	15.88	16.53	13.80	0.05	17.67	22.2	752	1
VTVS15GSMF	972	17.60	18.31	15.10	0.05	15.89	25	684	1
VTVS17GSMF	982	19.60	20.40	16.90	0.05	14.21	28	606	1
VTVS19GSMF	992	21.61	22.50	18.70	0.05	12.84	31	558	1
VTVS21GSMF	9A2	23.72	24.69	20.50	0.05	11.67	34	513	1
VTVS23GSMF	9B2	26.51	27.60	22.60	0.05	10.40	38	480	1
VTVS25GSMF	9C2	29.40	30.60	25.20	0.05	9.35	42	433	1
VTVS28GSMF	9D2	32.39	33.72	27.90	0.05	8.45	47	412	1
VTVS31GSMF	9E2	35.28	36.72	30.60	0.05	7.74	51	380	1
VTVS33GSMF	9F2	38.27	39.84	33.30	0.05	7.11	55	379	1
VTVS36GSMF	9G2	42.19	43.92	36.00	0.05	6.43	61	342	1
VTVS40GSMF	9H2	46.11	48.00	39.60	0.05	5.87	67	309	1
VTVS43GSMF	9J2	50.03	52.08	43.20	0.05	5.39	73	292	1
VTVS47GSMF	9K2	54.88	57.12	46.80	0.05	4.90	80	293	1
VTVS52GSMF	9L2	60.76	63.24	52.20	0.05	4.41	89	242	1
VTVS58GSMF	9M2	66.64	69.36	57.60	0.05	4.01	98	245	1
VTVS63GSMF	9N2	73.01	75.99	63.00	0.05	3.65	108	227	1

## Vishay Semiconductors

#### TYPICAL CHARACTERISTICS (T<sub>amb</sub> = 25 °C, unless otherwise specified)

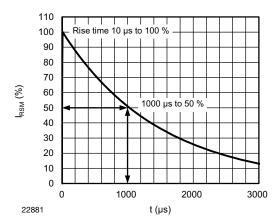


Fig. 1 - 10/1000 µs Peak Pulse Current Wave Form

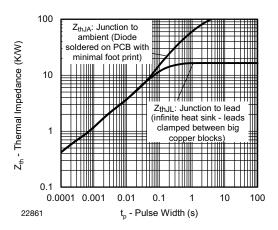


Fig. 2 - Thermal Impedance vs. Time

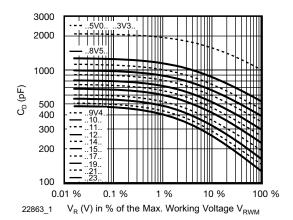


Fig. 3 - Typical Capacitance C<sub>D</sub> vs. Reverse Voltage V<sub>B</sub>

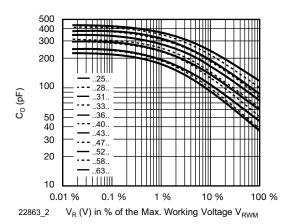


Fig. 4 - Typical Capacitance C<sub>D</sub> vs. Reverse Voltage V<sub>B</sub>

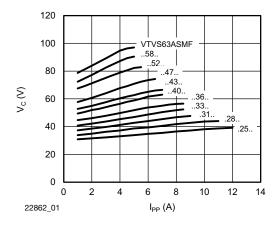


Fig. 5 - Typical Peak Clamping Voltage vs. Peak Pulse Current

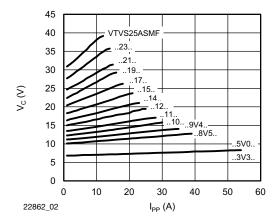


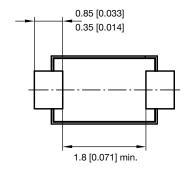
Fig. 6 - Typical Peak Clamping Voltage vs. Peak Pulse Current

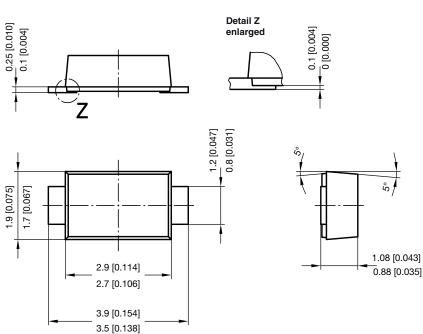


www.vishay.com

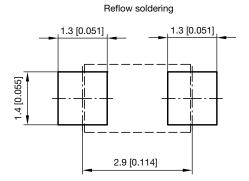
## Vishay Semiconductors

### PACKAGE DIMENSIONS in millimeters (inches): SMF (DO-219AB)





foot print recommendation:



Created - Date: 15. February 2005 Rev. 6 - Date: 24.Feb.2021

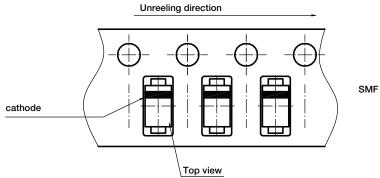
Document no.: S8-V-3915.01-001 (4)

22989



## Vishay Semiconductors

### **ORIENTATION IN CARRIER TAPE - SMF**



Document no.: S8-V-3717.02-003 (4) Created - Date: 09. Feb. 2010

22670